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Data Sheet

LED Chip Infrared

EOLC-980-11

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Radiation	Type	Electrodes
Infrared	AlGaAs/GaAs, MQW	P (anode) up

	<p>typ. dimensions</p> <p>typ thickness: 190±40 µm</p> <p>anode: gold alloy, 1.5 µm</p> <p>cathode: gold alloy, 0.5 µm structured, 25% covered</p>
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Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =100 mA	V _F		1.25		V
Forward voltage	I _F =350 mA	V _F		1.30		V
Reverse current	I _R =5 V	I _R			10	µA
Radiant power*	I _F =50 mA	Φ _e		4.5		mW
Radiant intensity*	I _F =350 mA	I _e		5		mW/sr
Peak wavelength	I _F =350 mA	λ _p		980		nm
FWHM	I _F =350 mA	λ _{0.5}		40		nm
Switching times	I _F =350 mA	t _r , t _f		20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 014



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.